

Modeling of the bipolar transistor under X-Ray pulse ionizing radiation

Thursday, 13 October 2016 15:15 (30)

This document describes a 2D model of the bipolar transistor 2T312 under X-ray pulse ionizing radiation. Both the Finite Element Discretization and Semiconductor module of Comsol 5.1 are used. We present an analysis of energy deposition in this device under X-ray and the results of transient ionizing current response for some different carrier densities.

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Session Classification : Poster session - IV

Track Classification : Methods of experimental physics